U.S. Department of Commerce, Patent and Trademark Office	Atty. Docket No.	Application No.
	NS-5127-1D US	10/699,221
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	Confirmation No.
Substitute Form PTO 1449	Bulucea, Constantin	2799
	Filing Date	Group
	31 October 2003	2814

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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	AF						
	AG						
	AH						

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
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	AK							
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Application No.
	NS-5127-1D US	10/699,221
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Foreign Patent Documents

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		Document	Date	Country	Class	Subclass	Yes	No
DF	AI	4-199682	07/1992	Japan	257	365		X
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Examiner	Date Considered
	12/17/05

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U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Application No.
	NS-5127-1D US	Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant	Confirmation No.
(Use several sheets if necessary)	Constantin Bulucea	Unknown
	Filing Date	Group
	Herewith	Unknown

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U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Application No.
	NS-5127-1D US	10/054,653
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant	Confirmation No.
(Use several sheets if necessary)	Constantin Bulucea	9448
	Filing Date	Group
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